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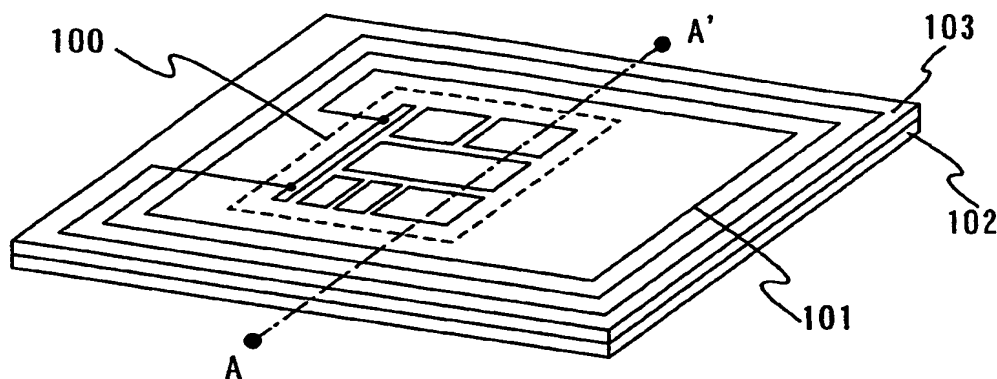
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(54) Title: SEMICONDUCTOR DEVICE



(57) Abstract: An object of the present invention is providing a semiconductor device that is capable of improving the reliability of a semiconductor element and enhancing the mechanical strength without suppressing the scale of a circuit. The semiconductor device includes an integrated circuit sandwiched between first and second sealing films, an antenna electrically connected to the integrated circuit, the first sealing film sandwiched between a substrate and the integrated circuit, which includes a plurality of first insulating films and at least one second insulating film sandwiched therebetween, the second sealing film including a plurality of third insulating films and at least one fourth insulating film sandwiched therebetween. The second insulating film has lower stress than the first insulating film and the fourth insulating film has lower stress than the third insulating film. The first and third insulating films are inorganic insulating films.

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